

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: To Be Assigned

Examiner: To Be Assigned

In re PATENT APPLICATION of:

Applicant(s) : Toshio NAGATA )

Appln. No. : To Be Assigned )

Filed : June 27, 2003 )

For : METHOD OF FABRICATING A )  
SEMICONDUCTOR DEVICE )  
INCLUDING A TUNNEL OXIDE FILM )

Atty. Dkt. : MAE 286 )

**INFORMATION  
DISCLOSURE  
STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

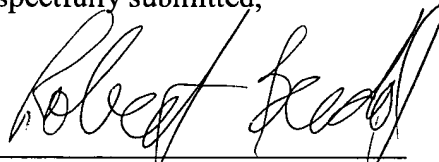
Sir:

This is an information disclosure statement submitted in compliance with the timing requirements of 37 C.F.R. §1.97(b)(1).

Attached is a copy of a Japanese publication. Any relevance of the Japanese publication can be gleaned from the attached English-language Abstract. The document is listed on the attached Form PTO-1449.

Since this Information Disclosure Statement is being filed with the application, no certification or fee is required, and the requirements of 37 C.F.R. §§1.97 and 1.98 are deemed to be fully met as to the document submitted. Consideration of the submitted document is respectfully requested.

Respectfully submitted,



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June 27, 2003  
Date

RHB:tz

FEE ENCLOSED: \$ 790  
Please charge any further  
fees to our Deposit Account  
N. 18-0002

<b>FORM PTO-1449</b>  <b>INFORMATION DISCLOSURE STATEMENT</b>				Atty Docket <b>MAE 286</b>		Application No. <b>To Be Assigned</b>	
				Applicant <b>Toshio NAGATA</b>			
				Filing Date <b>June 27, 2003</b>		Group Unit <b>To Be Assigned</b>	
<b>U.S. PATENT DOCUMENTS</b>							
Examiner Initial		Document Number	Date	Name	Class	Sub- Class	Filing Date
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
<b>FOREIGN PATENT DOCUMENTS</b>							
		Document Number	Date	Country	Class	Sub- Class	Trans- lation
	AH	08-255905	10/01/96				Abstract
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
<b>OTHER (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
	AO	James C.M. Hwang, "Relationship between gate lag, power drift, and power slump of pseudomorphic high electron mobility transistors", Solid-State Electronics 43 (1999), pp. 1325-1331					
	AP						
	AQ						
	AR						
Examiner					Date Considered		
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							